

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	46298	defect\$6 near10 (remov\$6 or clean\$6 or etch\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 20:01
L2	5175	defect\$6 near10 (resist or photoresist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 19:59
L3	1732	1 and 2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 19:59
L4	1781	2 same (thin\$6 or CMP or abrad\$6 or polish\$6 or mill\$6 or etch\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 20:05
L5	1049	3 and 4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 20:00
L6	977	5 and (@ad<"20040225" or @rlad<"20040225")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 20:00
L7	791	6 and (semiconductor GaSb or InAs or Si or silicon or InP or GaAs or InAs or AlSb)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 20:02
L8	394613	(resist or photoresist or protect\$6 or coat\$6) near10 (thin\$6 or CMP or abrad\$6 or polish\$6 or mill\$6 or etch\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 20:05
L9	757	7 and 8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 20:04

L10	262731	(resist or photoresist or protect\$6 or coat\$6) near10 (thin\$6 or CMP or abrad\$6 or polish\$6 or mill\$6 )	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 20:05
L11	279	9 and 10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 20:05

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L3	1732	1 and 2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 19:59
L4	1781	2 same (thin\$6 or CMP or abrad\$6 or polish\$6 or mill\$6 or etch\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 20:03
L5	1049	3 and 4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 20:00
L6	977	5 and (@ad<"20040225" or @rlad<"20040225")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 20:00
L7	791	6 and (semiconductor GaSb or InAs or Si or silicon or InP or GaAs or InAs or AlSb)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 20:02
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L9	757	7 and 8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 20:04